

TENTATIVE

Features and Applications

- Low ON-state resistance.
- 2.5V drive.

Absolute Maximum Ratings / Ta=25°C

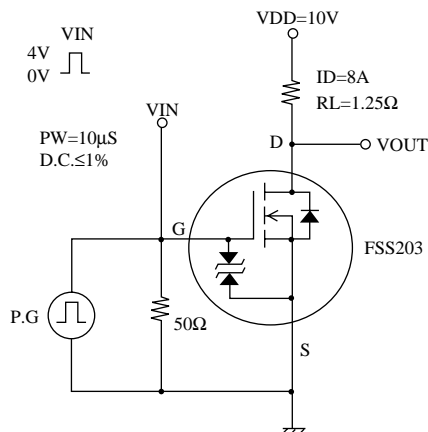
			unit	
Drain to Source Voltage	VDSS	20	V	
Gate to Source Voltage	VGSS	±10	V	
Drain Current(DC)	ID	8	A	
Drain Current(Pulse)	IDP	PW≤10μs,duty cycle≤1%	52	A
Allowable power Dissipation	PD	Mounted on ceramic board(1200mm ² ×0.8mm)1unit	2	W
Channel Temperature	Tch	150	°C	
Storage Temperature	Tstg	-55 to +150	°C	

Electrical Characteristics / Ta=25°C

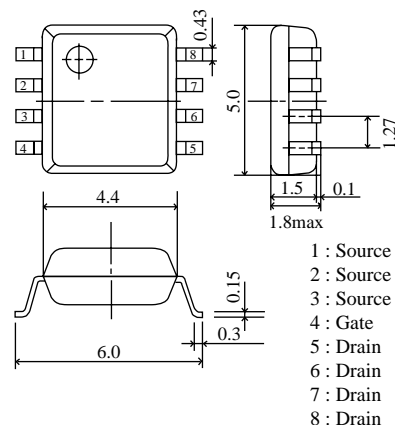
			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA , VGS=0	20			V
Zero Gate Voltage Drain Current	IDSS	VDS=20V , VGS=0			100	μA
Gate to Source Leakage Current	IGSS	VGS=±8V , VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V , ID=1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	VDS=10V , ID=8A	12	18		S
Static Drain to Source on State Resistance	RDS(on)1	ID=8A , VGS=4V		18	24	mΩ
	RDS(on)2	ID=A , VGS=2.5V		27	37	mΩ
Input Capacitance	Ciss	VDS=10V , f=1MHz		1000		pF
Output Capacitance	Coss	VDS=10V , f=1MHz		700		pF
Reverse Transfer Capacitance	Crss	VDS=10V , f=1MHz		400		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit		20		ns
Rise Time	tr			300		ns
Turn-off Delay Time	td(off)			200		ns
Fall Time	tf			200		ns
Total Gate Charge	Qg	VDS=10V , VGS=10V , ID=8A		44		nC
Gate Source Charge	Qgs			5		nC
Gate Drain Charge	Qgd			7		nC
Diode Forward Voltage	VSD	IS=8A , VGS=0	1.0	1.2		V

Marking : S203

Switching Time Test Circuit



Package Dimensions
SOP8(unit:mm)



Specifications and information herein are subject to change without notice.

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